2SB1299

Silicon PNP epitaxial planar type

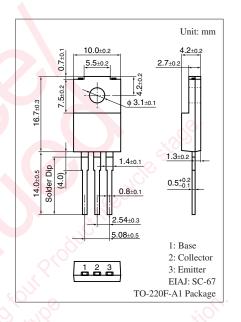
For power amplification

■ Features

- High forward current transfer ratio h_{FE}
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol Rating		Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V_{CEO}	-60	V	
Emitter-base voltage (Collector open)	V_{EBO}	-6	V	
Collector current	I_{C}	-3	A	
Peak collector current	I_{CP}	-6	A	
Base current	I_{B}	-1	A	
Collector power $T_C = 25^{\circ}C$	P _C	40	W	
dissipation		2		
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

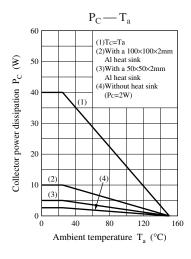
Symbol	Conditions	Min	Тур	Max	Unit
V_{CEO}	$I_C = -25 \text{ mA}, I_B = 0$	-60	35		V
I_{CBO}	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
I_{CEO}	$V_{CE} = -40 \text{ V}, I_B = 0$	7.7		-100	μΑ
I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-100	μΑ
h_{FE}	$V_{CE} = -4 \text{ V}, I_C = -0.5 \text{ A}$	300		700	_
V _{CE(sat)}	$I_C = -2 A, I_B = -0.05 A$			-1	V
f_T	$V_{CE} = -12 \text{ V}, I_C = -0.2 \text{ A}, f = 10 \text{ MHz}$		30		MHz
	V_{CEO} I_{CBO} I_{CEO} I_{EBO} h_{FE} $V_{CE(sat)}$	$\begin{split} &V_{CEO} &I_{C} = -25 \text{ mA}, I_{B} = 0 \\ &I_{CBO} &V_{CB} = -60 \text{ V}, I_{E} = 0 \\ &I_{CEO} &V_{CE} = -40 \text{ V}, I_{B} = 0 \\ &I_{EBO} &V_{EB} = -6 \text{ V}, I_{C} = 0 \\ &h_{FE} &V_{CE} = -4 \text{ V}, I_{C} = -0.5 \text{ A} \\ &V_{CE(sat)} &I_{C} = -2 \text{ A}, I_{B} = -0.05 \text{ A} \end{split}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccc} V_{CEO} & I_{C} = -25 \text{ mA}, I_{B} = 0 & -60 \\ \\ I_{CBO} & V_{CB} = -60 \text{ V}, I_{E} = 0 \\ \\ I_{CEO} & V_{CE} = -40 \text{ V}, I_{B} = 0 \\ \\ I_{EBO} & V_{EB} = -6 \text{ V}, I_{C} = 0 \\ \\ h_{FE} & V_{CE} = -4 \text{ V}, I_{C} = -0.5 \text{ A} \\ \\ V_{CE(sat)} & I_{C} = -2 \text{ A}, I_{B} = -0.05 \text{ A} \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

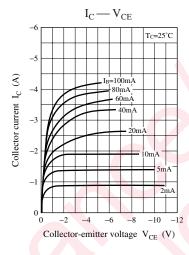
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

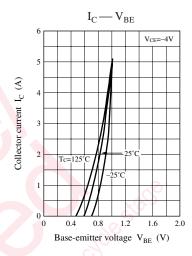
2. *: Rank classification

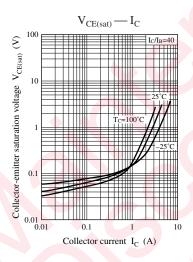
Rank	Q	P
h_{FE}	300 to 500	400 to 700

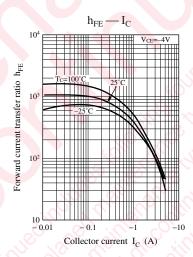
Panasonic

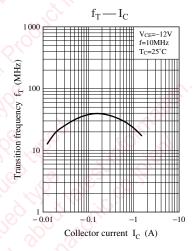


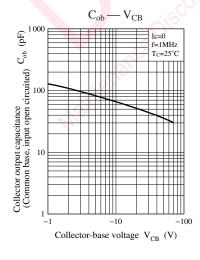


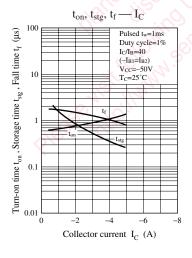


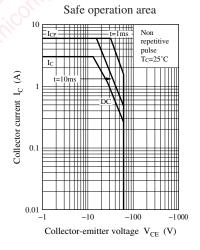




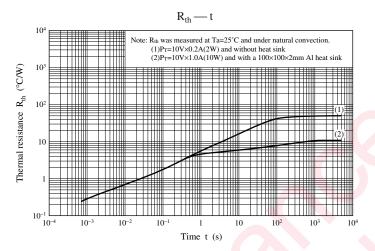








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